

Features

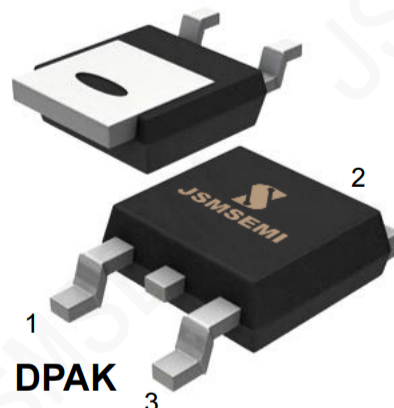
- Zero Forward/Reverse Recovery Current
- High Blocking Voltage
- High Frequency Operation
- Positive Temperature Coefficient on V_F
- Temperature Independent Switching Behavior
- High surge current capability

Benefits

- Higher System Efficiency
- Parallel Device Convenience without thermal runaway
- Higher Temperature Application
- No Switching loss
- Hard Switching & Higher Reliability
- Environmental Protection

Applications

- Motor Drives
- Solar / Wind Inverters
- AC/DC converters
- DC/DC converters
- Uninterruptable power supplies



Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}		650	V
Peak Reverse Surge Voltage	V_{RSM}		650	V
DC Blocking Voltage	V_R		650	V
Continuous Forward Current	I_F	$T_C=25^\circ\text{C}$ $T_C=135^\circ\text{C}$ $T_C=150^\circ\text{C}$	38 16 10	A
Non repetitive Forward Surge Current	I_{FSM}	$T_C = 25^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse $T_C = 110^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse $T_C = 25^\circ\text{C}$, $t_p=10$ μs , Square	65 55 520	A
Repetitive peak Forward Surge Current	I_{FRM}	$T_C = 25^\circ\text{C}$, $t_p=10$ ms, Freq = 0.1Hz, 100 cycles, Half Sine Pulse $T_C = 110^\circ\text{C}$, $t_p=10$ ms, Freq = 0.1Hz, 100 cycles, Half Sine Pulse	55 45	A
Total power dissipation	P_D	$T_C=25^\circ\text{C}$	107	W
Operating Junction Temperature	T_J		-55 to 175	$^\circ\text{C}$
Storage Temperature	T_{STG}		-55 to 175	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Electrical Characteristics

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
DC Blocking Voltage	V_{DC}	$I_R = 250\mu A, T_J = 25^\circ C$	650			V
Forward Voltage	V_F	$I_F = 10A, T_J = 25^\circ C$		1.45	1.8	V
		$I_F = 10A, T_J = 125^\circ C$		1.55		
		$I_F = 10A, T_J = 175^\circ C$		1.7		V
Reverse Current	I_R	$V_R = 650V, T_J = 25^\circ C$		12	80	μA
		$V_R = 650V, T_J = 125^\circ C$		68		μA
		$V_R = 650V, T_J = 175^\circ C$		190		μA
Total Capacitive Charge	Q_C	$V_R = 400V, I_F = 10A, di/dt = 200A/\mu s, T_J = 25^\circ C$		23		nC
Total Capacitance	C	$V_R = 1V, T_J = 25^\circ C, Freq = 1MHz$		380		pF
		$V_R = 300V, T_J = 25^\circ C, Freq = 1MHz$		38		
		$V_R = 550V, T_J = 25^\circ C, Freq = 1MHz$		31		

Note: This is a majority carrier diode, so there is no reverse recovery charge

Thermal Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Thermal Resistance	$R_{th(j-c)}$	junction-case		1.4		$^\circ C/W$

Ordering Information

Order number	Package	Marking	Operation Temperature Range	MSL Grade	Ship,Quantity	Green
SSTPSC8H065BY-TR	TO-252	SC6D10065E	-55 to 175 $^\circ C$	1	T&R,2500	RoHS

Typical Electrical Curves

Figure 1. Forward Characteristics

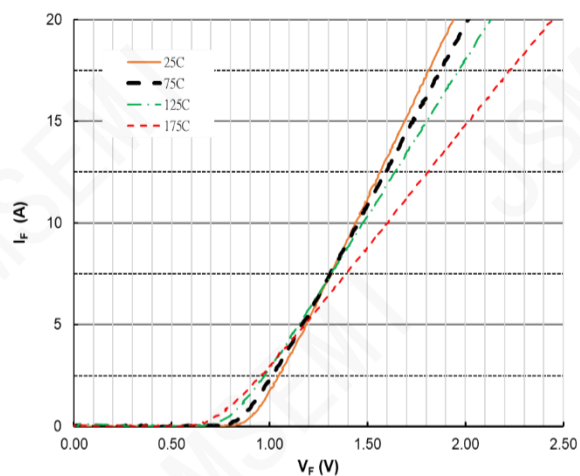


Figure 2. Forward Characteristics

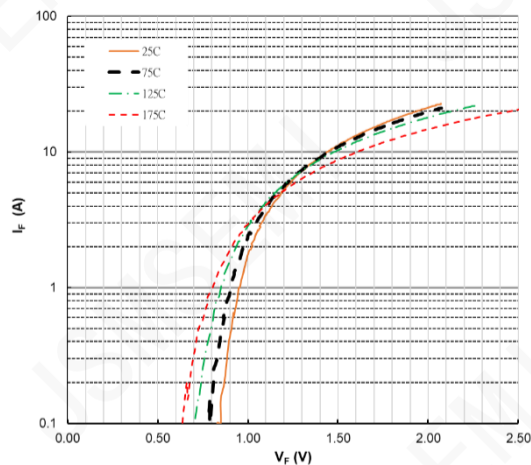


Figure 3. Reverse Characteristics

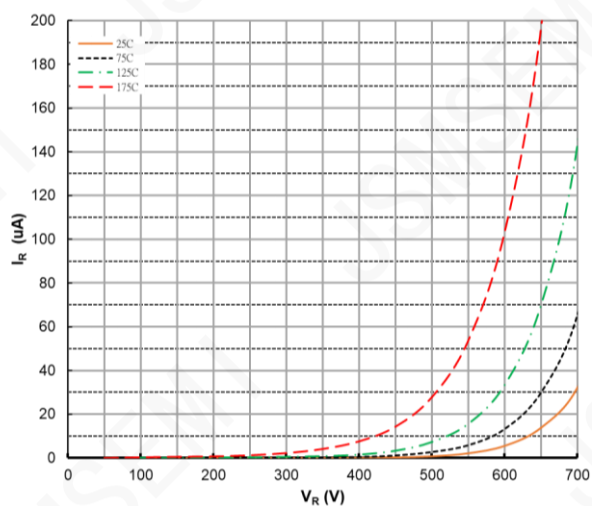


Figure 4. Power Derating

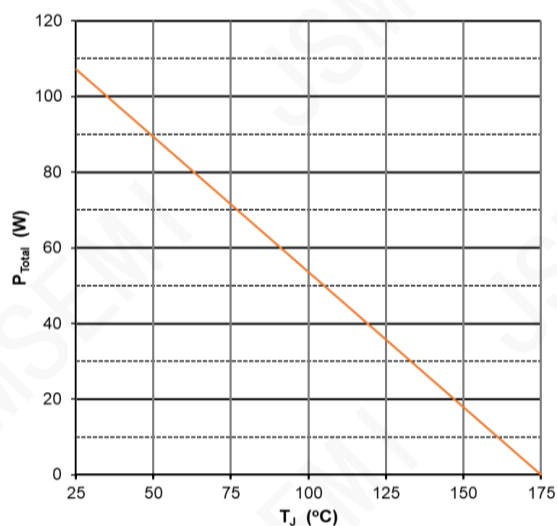


Figure 5. Capacitance vs Reverse Voltage

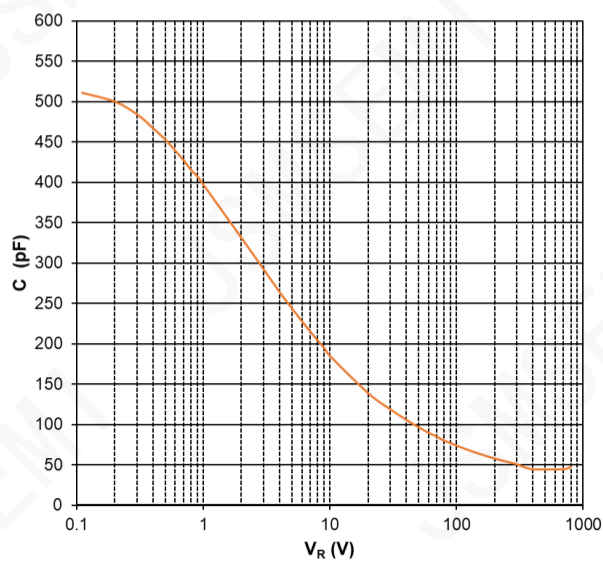
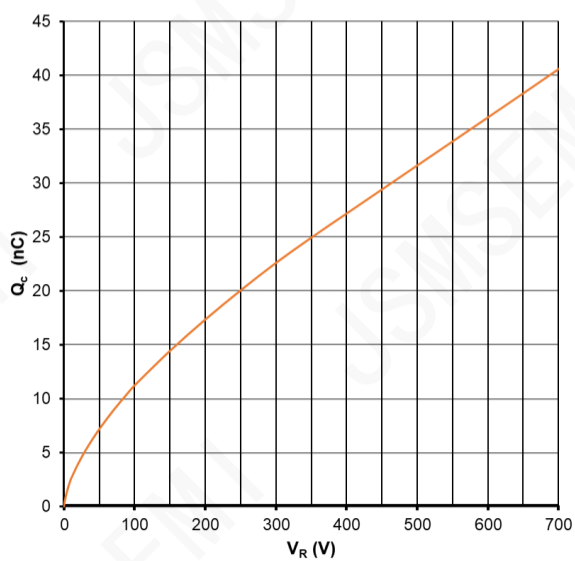
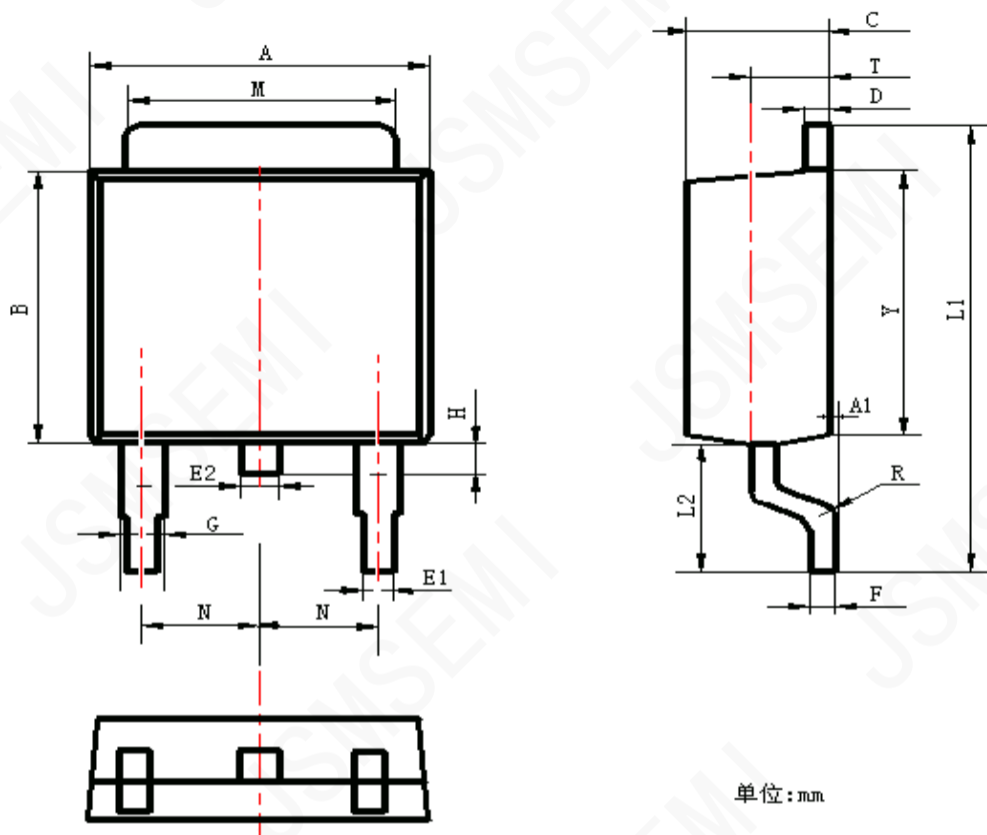


Figure 6. Recovery Charge vs Reverse Voltage



TO-252 Package Information



单位:mm

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	6.30	6.90	0.248	0.272
A1	0.00	0.16	0.000	0.006
B	5.70	6.30	0.224	0.248
C	2.10	2.50	0.083	0.098
D	0.30	0.70	0.012	0.028
E1	0.60	0.90	0.024	0.035
E2	0.70	1.00	0.028	0.039
F	0.30	0.60	0.012	0.024
G	0.70	1.20	0.028	0.047
L1	9.60	10.50	0.378	0.413
L2	2.70	3.10	0.106	0.122
H	0.40	1.00	0.016	0.039
M	5.10	5.50	0.201	0.217
N	2.09	2.49	0.082	0.098
R	0.30		0.012	
T	1.40	1.60	0.055	0.063
Y	5.10	6.30	0.201	0.248

Revision History

Rev.	Change	Date
V1.0	Initial version	2/23/2022

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